General Description

The GreenMOS® high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

Features

GreenMOS®

- Low $R_{DS(ON)}$ & FOM
- Ultra-low Q_{rr}
- Extremely low switching loss
- Excellent stability and uniformity

RoHS compliant

Applications

- LED lighting
- Adapter
- Telecom
- Solar/UPS
- Sever

Key Performance Parameters

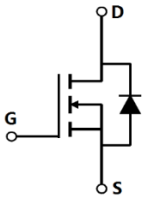
Parameter	Value	Unit
$V_{DS,\ min}$ @ $T_{j(max)}$	650	V
$I_{D,\ pulse}$	156	A
$R_{DS(ON),\ max}$ @ V_{GS}=10V	60	mΩ
Q_g	135	nC

Marking Information

Product Name	Package	Marking
OSG60R060HMF	TO247	OSG60R060HM

Package & Pin Information





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Absolute Maximum Ratings at T_j=25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	600	V
Gate-source voltage	V_{GS}	±30	V
Continuous drain current[1], T_C=25 °C	I_D	52	A
Continuous drain current[1], T_C=100 °C		32.8	
Pulsed drain current[2], T_C=25 °C	$I_{D,\ pulse}$	156	A
Continuous diode forward current[1], T_C=25 °C	I_S	52	A
Diode pulsed current[2], T_C=25 °C	$I_{S,\ pulse}$	156	A
Power dissipation[3], T_C=25 °C	P_D	440	W
Single pulsed avalanche energy[5]	E_{AS}	486	mJ
MOSFET dv/dt ruggedness, V_{DS}=0…480 V	dv/dt	50	V/ns
Reverse diode dv/dt, V_{DS}=0…480 V, I_{SD}≤I_D	dv/dt	50	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.28	°C/W
Thermal resistance, junction-ambient[4]	$R_{\theta JA}$	62	°C/W

Electrical Characteristics at T_j=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	600			V	V_{GS}=0 V, I_D=1 mA
		650				V_{GS}=0 V, I_D=1 mA, T_j=150 °C
Gate threshold voltage	$V_{GS(th)}$	2.0		4.0	V	V_{DS}=V_{GS}, I_D=1 mA
Drain-source on-state resistance	$R_{DS(ON)}$		50	60	mΩ	V_{GS}=10 V, I_D=26 A
			129			V_{GS}=10 V, I_D=26 A, T_j=150 °C
Gate-source leakage current	I_{GSS}			100	nA	V_{GS}=30 V
				-100		V_{GS}=-30 V
Drain-source leakage current	I_{DSS}			10	μA	V_{DS}=600 V, V_{GS}=0 V
Gate resistance	R_G		2		Ω	f=1 MHz, Open drain

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Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		4330		pF	V_{GS}=0 V, V_{DS}=50 V, f=100 kHz
Output capacitance	C_{oss}		290		pF	
Reverse transfer capacitance	C_{rss}		5		pF	
Effective output capacitance, energy related	$C_{o(er)}$		180		pF	V_{GS}=0 V, V_{DS}=0 V-400 V
Effective output capacitance, time related	$C_{o(tr)}$		840		pF	
Turn-on delay time	$t_{d(on)}$		16		ns	V_{GS}=18 V, V_{DS}=400 V, R_G=2 Ω, I_D=40 A
Rise time	t_r		19		ns	
Turn-off delay time	$t_{d(off)}$		33		ns	
Fall time	t_f		39		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		135		nC	V_{GS}=18 V, V_{DS}=400 V, I_D=40 A
Gate-source charge	Q_{gs}		53		nC	
Gate-drain charge	Q_{gd}		27		nC	
Gate plateau voltage	$V_{plateau}$		11.5		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.3	V	I_S=52 A, V_{GS}=0 V
Reverse recovery time	t_{rr}		182		ns	V_R=400 V, I_S=40 A, di/dt=100 A/μs
Reverse recovery charge	Q_{rr}		652		nC	
Peak reverse recovery current	I_{rrm}		6.5		A	

Note

1) Calculated continuous current based on maximum allowable junction temperature.
2) Repetitive rating; pulse width limited by max. junction temperature.
3) Pd is based on max. junction temperature, using junction-case thermal resistance.
4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_a=25 °C.
5) V_{DD}=100 V, V_{GS}=10 V, L=75 mH, starting T_j=25 °C.

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Electrical Characteristics Diagrams

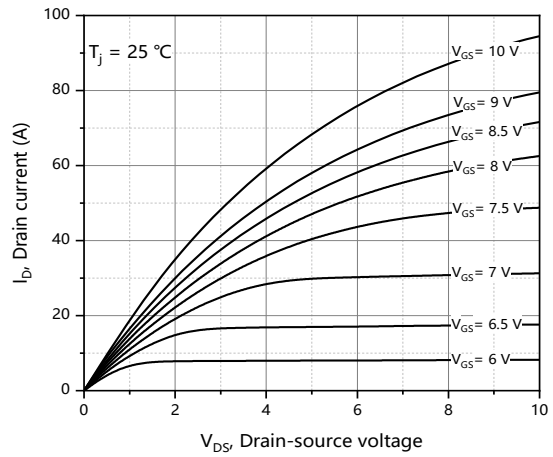

Figure 1. Typ. output characteristics

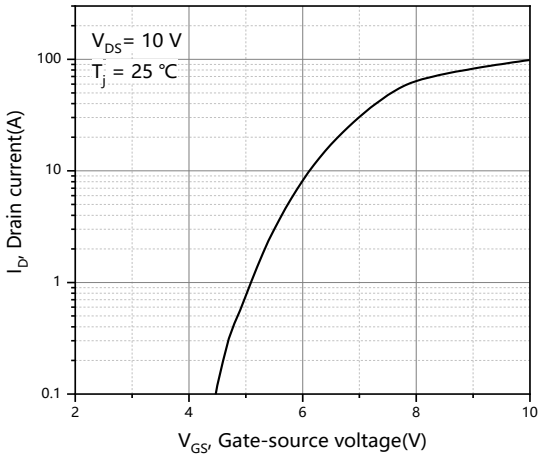

Figure 2. Typ. transfer characteristics

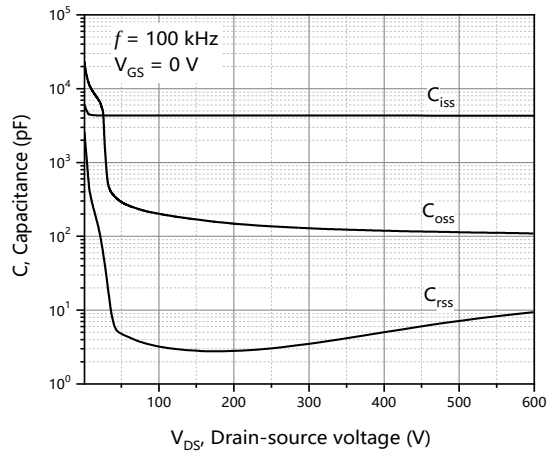

Figure 3. Typ. capacitances

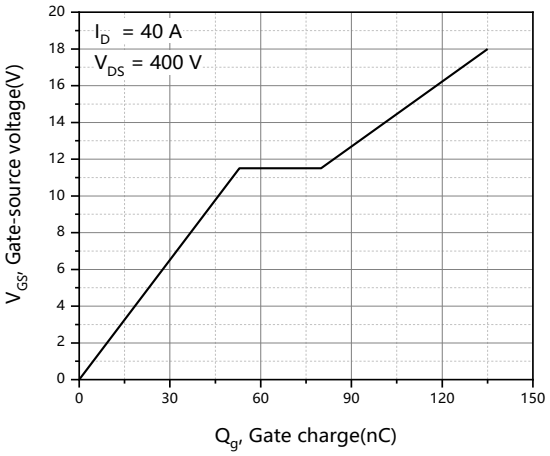

Figure 4. Typ. gate charge

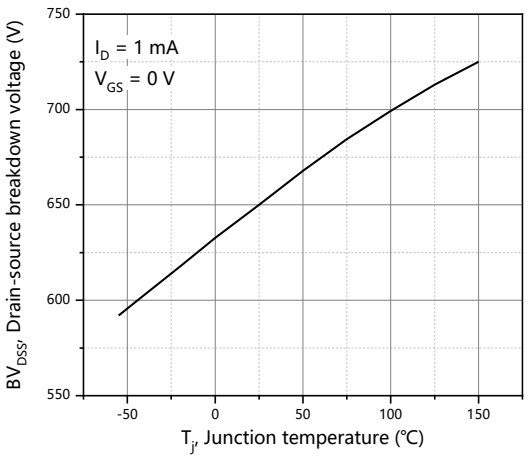

Figure 5. Drain-source breakdown voltage

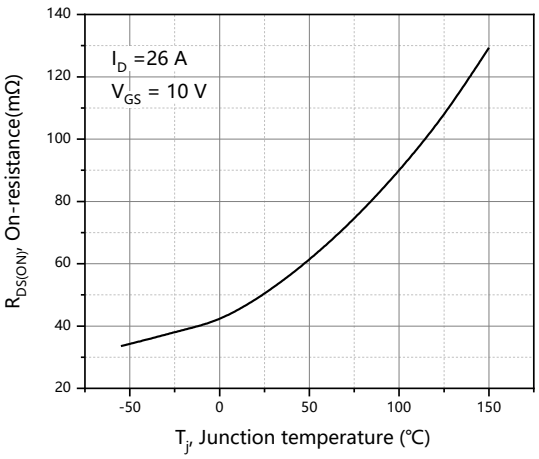

Figure 6. Drain-source on-state resistance

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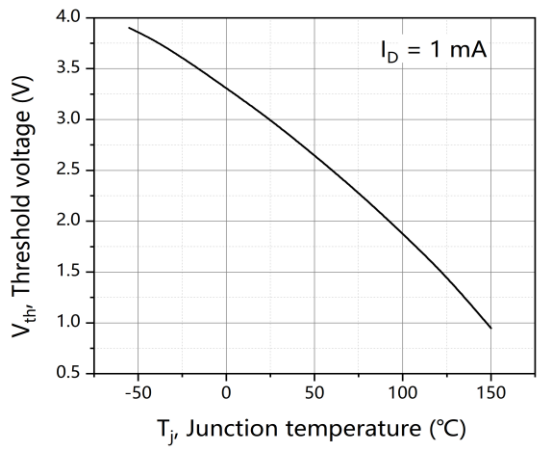

Figure 7. Threshold voltage

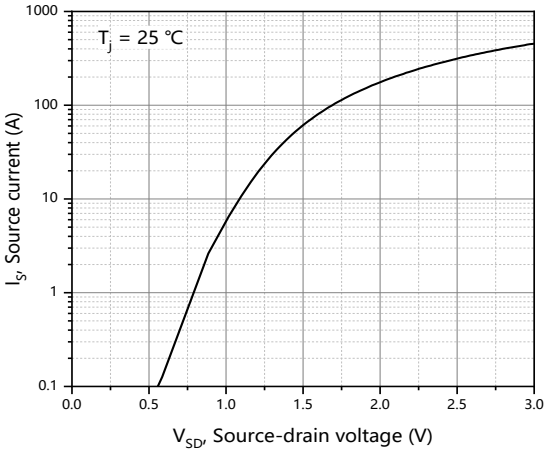

Figure 8. Forward characteristic of body diode

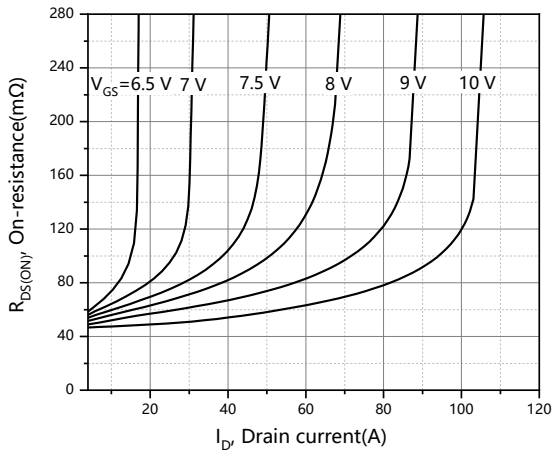

Figure 9. Drain-source on-state resistance

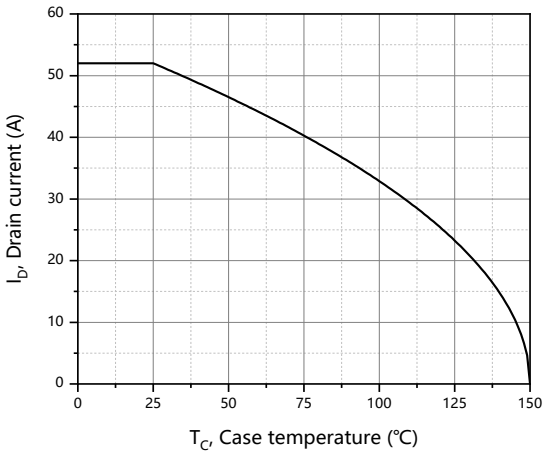

Figure 10. Drain current

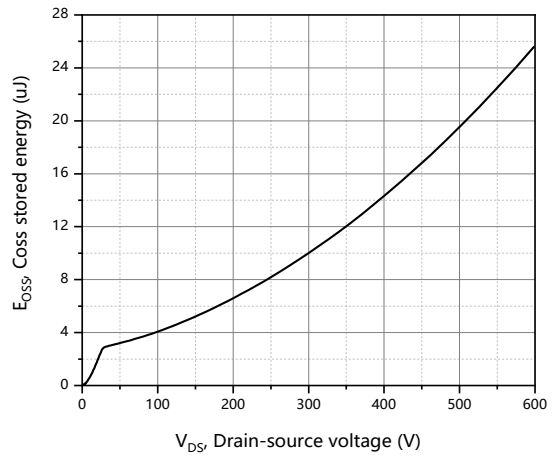

Figure 11. Typ. Coss stored energy

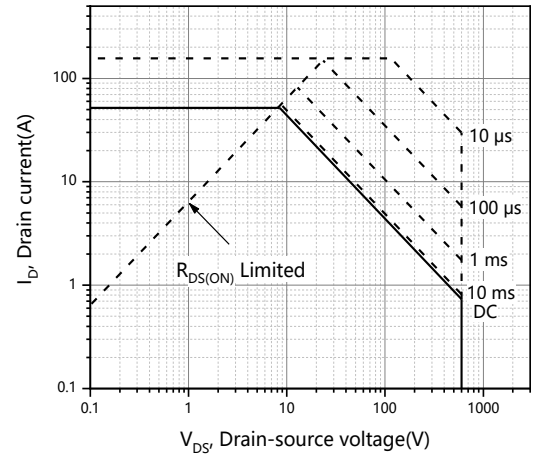

Figure 12. Safe operation area T_C=25 °C

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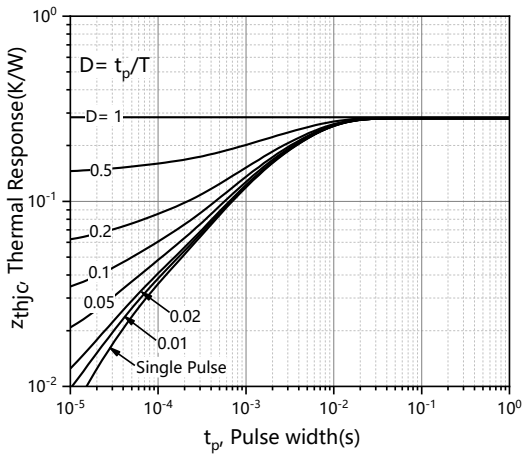

Figure 13. Max. transient thermal impedance

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Test circuits and waveforms

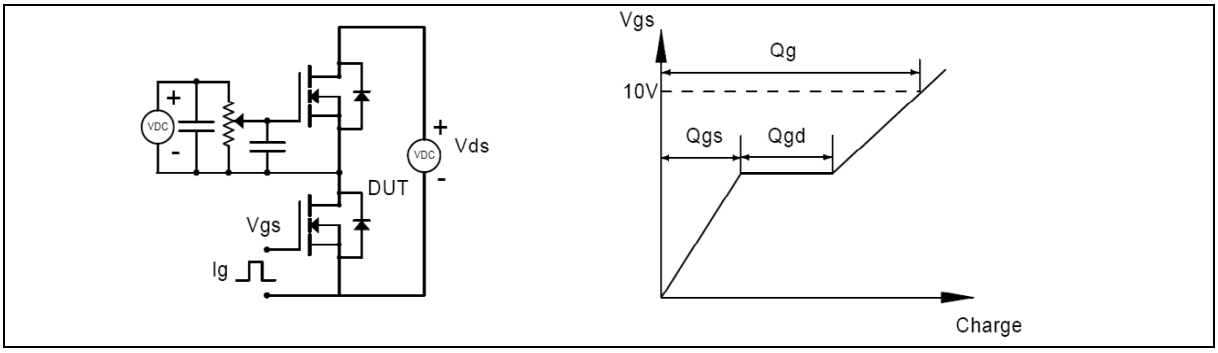

Figure 1. Gate charge test circuit & waveform

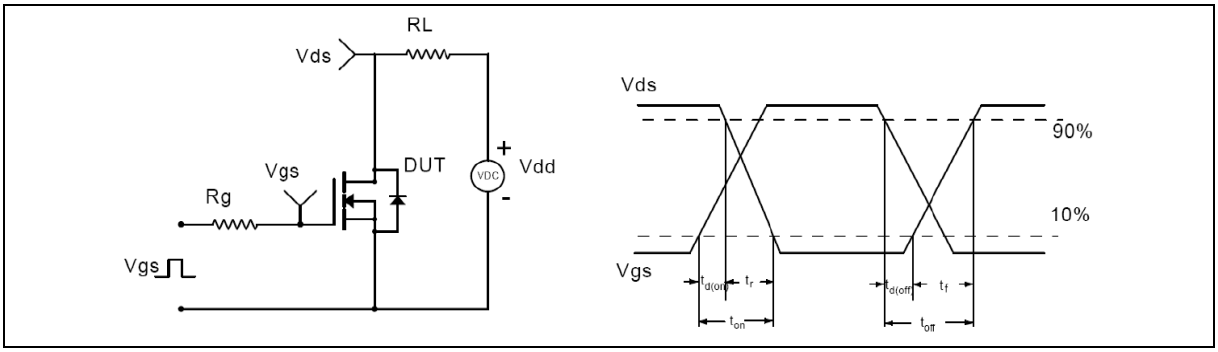

Figure 2. Switching time test circuit & waveforms

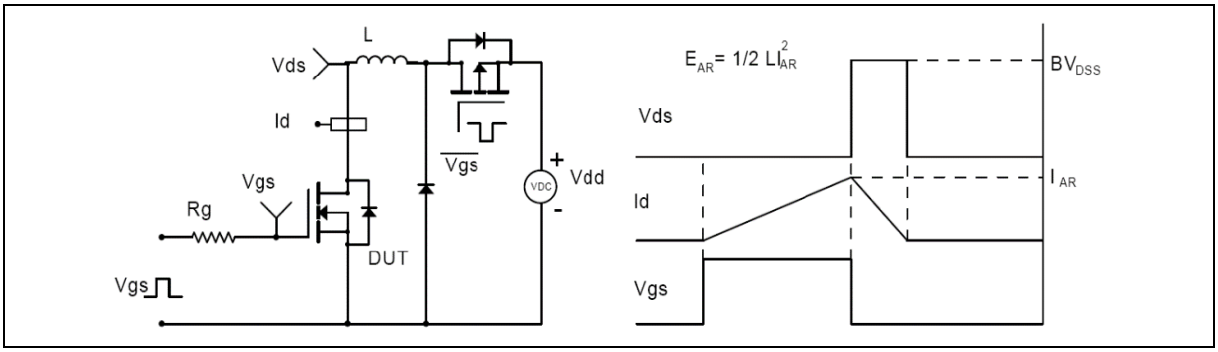

Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

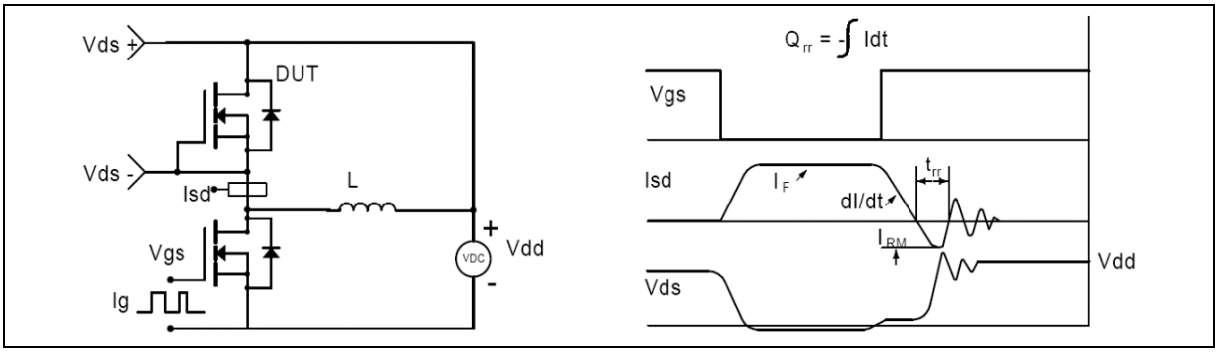

Figure 4. Diode reverse recovery test circuit & waveforms

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